## MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

## **VHF/UHF Transistor**

## **NPN Silicon**

#### Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	25	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	30	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	Vdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	R <sub>θJA</sub>	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina

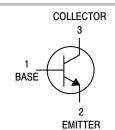


## **ON Semiconductor®**

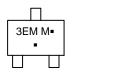
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SOT-23 (TO-236) CASE 318 STYLE 6



#### MARKING DIAGRAMS



MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-04LT1G

3E4 M•

3EM, 3E4= Specific Device Code M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10-4LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10LT3G, SMMBTH10-4LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

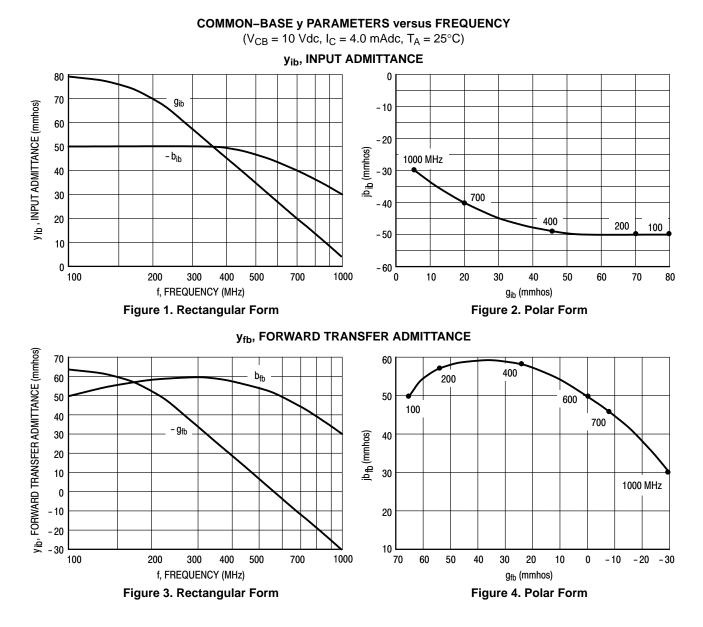
## MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	25	-	_	Vdc
Collector–Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	30	-	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \ \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	3.0	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 25 \text{ Vdc}, I_E = 0$ )	I <sub>CBO</sub>	_	_	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 2.0 \text{ Vdc}, I_C = 0$ )	I <sub>EBO</sub>	_	_	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 4.0 mAdc, V <sub>CE</sub> = 10 Vdc) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	h <sub>FE</sub>	60 120		_ 240	-
Collector–Emitter Saturation Voltage $(I_C = 4.0 \text{ mAdc}, I_B = 0.4 \text{ mAdc})$	V <sub>CE(sat)</sub>	-	_	0.5	Vdc
Base–Emitter On Voltage $(I_C = 4.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	V <sub>BE</sub>	_	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS	•			•	•
Current–Gain – Bandwidth Product (I <sub>C</sub> = 4.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 Mhz) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10–4LT1G, SMMBTH10–4LT3G	fT	650 800			MHz
Collector–Base Capacitance ( $V_{CB}$ = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	_	_	0.7	pF
Common–Base Feedback Capacitance $(V_{CB}$ = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>rb</sub>	_	_	0.65	pF
Collector Base Time Constant ( $I_C$ = 4.0 mAdc, $V_{CB}$ = 10 Vdc, f = 31.8 MHz)	rb′C <sub>c</sub>	_	_	9.0	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L



#### **TYPICAL CHARACTERISTICS**

## MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

#### **TYPICAL CHARACTERISTICS**

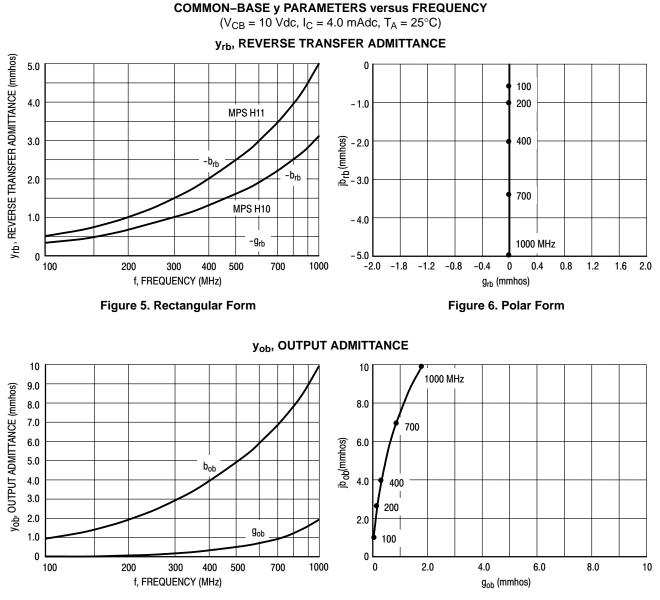


Figure 7. Rectangular Form

Figure 8. Polar Form

#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

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TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

## onsemi



SCALE 4:1

A\_\_\_\_ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS		INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*





XXX = Specific Device Code

M = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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## MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

# onsemi

#### SOT-23 (TO-236) CASE 318 ISSUE AT

#### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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